

## Claims

1. Method for etching a substrate, comprising placing said substrate in an etching chamber, introducing a first etchant and/or etch catalyst originating from a first source into  
5 said etching chamber, introducing a second etchant and/or etch catalyst originating from a second source, flushing said etching chamber following etching and removing said substrate, wherein the first etchant and/or etch catalyst is fed to the etching chamber from the first source through an auxiliary chamber, characterised in that the second etchant and/or etch catalyst is supplied through another path to said etching chamber and in that passing off said  
10 first etchant and/or etch catalyst through the auxiliary chamber is realised intermittently such that there is never a direct connection between the etching chamber and said first source.
2. Method according to Claim 1 wherein, after treatment of said substrate, flushing of said etching chamber is carried out via said auxiliary chamber.
3. Method according to one of the preceding claims, wherein the feed of said other  
15 reactant and/or other catalyst to said chamber is shut off when said auxiliary chamber is connected to said etching chamber.
4. Method according to one of the preceding claims, wherein the first reactant is HF.
5. Installation for etching a substrate (32), comprising an etching chamber (1)  
20 provided with an entry/exit opening (30) for said substrate, an inlet/discharge opening (2) for reactants and/or catalyst connected to a piping system for the separate supply of at least two reactants and/or catalysts, one feed comprising an auxiliary chamber (17) provided with an inlet and outlet each having a controller regulated shut-off valve (15, 16), the outlet being connected to the etching chamber and the inlet to the reactant and/or catalyst feed,  
25 characterised in that said controller is realised such that only one of said valves (15, 16) can be opened.
6. Installation according to Claim 5, wherein a bypass line (18) for said auxiliary chamber is present.
7. Installation according to Claim 5 or 6, wherein said etching chamber is connected  
30 to a vacuum pump (12).

9. Installation according to one of Claims 5 - 8, wherein said etching chamber comprises a construction which takes the vacuum in said etching chamber and is made exclusively of plastic.

10. Installation according to Claim 9, wherein said plastic construction comprises 5 polyvinylidene fluoride.

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